Sheet 1 of 4 MOV 0 8 2004 PTO-1449 REPRODUCED ATTORNEY DOCKET NO. APPLICATION NO. SUPPLEMENTAL INFORMATION DISCOSURE CITATION IN AN APPLICATION 0717.2033-002 10/608,780 FIRST NAMED INVENTOR FILING DATE June 27, 2003 Jagdish Narayan November 4, 2004 CONFIRMATION NO. GROUP **EXAMINER** Nhu, David 8117 2818 (Use several sheets if necessary)

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	AF9	6,118,801	09-12-2000	Ishikawa <i>et al</i> .
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November 4, 2004 (Use several sheets if necessary)	EXAMINER Nhu, David	CONFI 8117	RMATION NO.	GROUP 2818

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